

Sample &

Buy



LF412-N

SNOSBH7F-APRIL 1999-REVISED SEPTEMBER 2014

# LF412-N Low Offset, Low Drift Dual JFET Input Operational Amplifier

Technical

Documents

#### 1 Features

- Internally Trimmed Offset Voltage: 1 mV (Max)
- Input Offset Voltage Drift: 7 µV/°C (Typ)
- Low Input Bias Current: 50 pA
- Low Input Noise Current: 0.01 pA / VHz
- Wide Gain Bandwidth: 3 MHz (Min)
- High Slew Rate: 10V/µs (Min)
- Low Supply Current: 1.8 mA/Amplifier
- High Input Impedance: 10<sup>12</sup>Ω
- Low Total Harmonic Distortion: ≤0.02%
- Low 1/f Noise Corner: 50 Hz
- Fast Settling Time to 0.01%: 2 µs

#### Applications 2

- **High Speed Integrators**
- Fast D/A Converters
- Sample and Hold Circuits

## 3 Description

Tools &

Software

These devices are low cost, high speed, JFET input operational amplifiers with very low input offset voltage and input offset voltage drift. They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF412-N dual is pin compatible with the LM1558, allowing designers to immediately upgrade the overall performance of existing designs.

Support &

Community

20

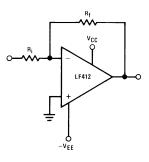
These amplifiers may be used in applications such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage and drift, low input bias current, high input impedance, high slew rate and wide bandwidth.

### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
LF412ACN	PDIP	9.59 mm x 6.35 mm
LF412CN	PDIP	9.59 mm x 6.35 mm
LF412MH	ТО	9.14 mm diameter

(1) For all available packages, see the orderable addendum at the end of the datasheet.

### **Inverting Amplifier**





TEXAS INSTRUMENTS

www.ti.com

# **Table of Contents**

1	Feat	tures 1
2	Арр	lications 1
3	Des	cription1
4	Rev	ision History 2
5	Pin	Configuration and Functions 2
6	Spe	cifications
	6.1	Absolute Maximum Ratings 4
	6.2	Handling Ratings 4
	6.3	Recommended Operating Conditions 4
	6.4	Thermal Information 5
	6.5	DC Electrical Characteristics5
	6.6	AC Electrical Characteristics 5
	6.7	Typical Characteristics 7
7	Deta	ailed Description 12
	7.1	Overview 12

	7.2	Functional Block Diagram 1	2
	7.3	Feature Description 1	2
	7.4	Device Functional Modes 1	3
8		lication and Implementation1	
	8.1	Application Information 1	4
		Typical Application 1	
9	Pow	er Supply Recommendations1	6
10	Layo	out 1	6
	10.1	Layout Guidelines 1	6
	10.2	Layout Example 1	6
11	Devi	ice and Documentation Support 1	7
	11.1	Trademarks 1	7
	11.2	Electrostatic Discharge Caution 1	7
	11.3	Glossary1	7
12	Мес	hanical, Packaging, and Orderable	
	Infor	mation 1	7

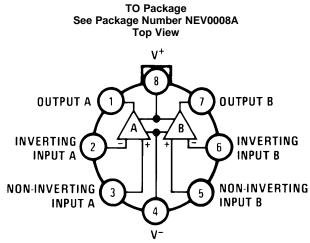
## **4** Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (March 2014) to Revision F	Page
Updated datasheet to new TI layout	1
Deleted note.	
- Deleted $\Delta V_{OS}/\Delta T$ Max specification for LF412A.	
- Deleted $\Delta V_{OS}/\Delta T$ Max specification for LF412.	
Added Application Note	14
Changes from Revision D (March 2013) to Revision E	Page

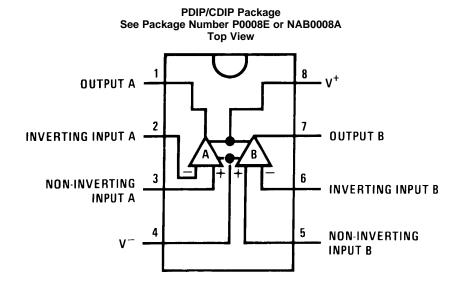
•	Changed layout of National Data Sheet to TI format	14
---	--	----

# 5 Pin Configuration and Functions



Note. Pin 4 connected to case.





### **Pin Functions**

PI	PIN I/O		DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
Output A	1	0	Amplifier A Output
Inverting Input A	2	I	Amplifier A Inverting Input
Non-Inverting Input A	3	I	Amplifier A Non-Inverting Input
V-	4	Р	Negative Supply
Non-Inverting Input B	5	I	Amplifier B Non-Inverting Input
Inverting Input B	6	I	Amplifier B Inverting Input
Output B	7	0	Amplifier B Output
V+	8	Р	Positive Supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

	LF4	12A	LF412		UNIT
	MIN         MAX         MIN           -22         22         -18           -38         38         -30           Continuous         Continuous         Continuous           TO Package         PDIP P           See <sup>(6)</sup> 6           150         1	MAX	UNIT		
Supply Voltage	-22	22	-18	18	V
Differential Input Voltage	-38	38	-30	30	V
Input voltage Range <sup>(3)</sup>					
Output Short Circuit Duration <sup>(4)</sup>	Continuous		Continuous		
	TO Package		PDIP P	ackage	
Power Dissipation <sup>(5)</sup>	Se	e <sup>(6)</sup>	670		mW
T <sub>j</sub> max	150		1	15	°C
Operating Temp. Range	Se	e <sup>(7)</sup>	Se	e <sup>(7)</sup>	
Lead Temp. (Soldering, 10 sec.)	2	60	2	60	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Refer to RETS412X for LF412MH and LF412MJ military specifications.

(3) Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

(4) Any of the amplifier outputs can be shorted to ground indefinitely, however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

(5) Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the part to operate outside guaranteed limits.

(6) For operating at elevated temperature, these devices must be derated based on a thermal resistance of  $\theta_{iA}$ .

(7) These devices are available in both the commercial temperature range 0°C≤T<sub>A</sub>≤70°C and the military temperature range -55°C≤T<sub>A</sub>≤125°C. The temperature range is designated by the position just before the package type in the device number. A "C" indicates the commercial temperature range and an "M" indicates the military temperature range. The military temperature range is available in TO package only. In all cases the maximum operating temperature is limited by internal junction temperature T<sub>i</sub> max.

### 6.2 Handling Ratings

			TO and PD	IP Package		
			MIN			
T <sub>stg</sub>	Storage temperature rar	ge	-65	150	°C	
	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	-1700	1700 <sup>(2)</sup>	Ň	
V <sub>(ESD)</sub>		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(3)</sup>				

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) Human body model, 1.5 k $\Omega$  in series with 100 pF.

(3) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Supply Voltage LF412A			±20	V
Supply Voltage LF412			±15	V

## 6.4 Thermal Information

	THERMAL METRIC <sup>(1)</sup>	TO Package	PDIP Package	UNIT
$R_{\thetaJA}$	Junction-to-ambient thermal resistance (Typical)	152	115	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance			
$R_{\theta JB}$	Junction-to-board thermal resistance			°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter			°C/VV
$\Psi_{JB}$	Junction-to-board characterization parameter			
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance			

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

# 6.5 DC Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

				L	.F412A <sup>(1)</sup>		I	_F412 <sup>(1)</sup>		
	PARAMETER	TEST CON	IDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V <sub>OS</sub>	Input Offset Voltage	$R_S=10 \text{ k}\Omega, T_A=25^{\circ}$	С		0.5	1.0		1.0	3.0	mV
$\Delta V_{OS}/\Delta$ T	Average TC of Input Offset Voltage	R <sub>S</sub> =10 kΩ			7			7		µV/°C
			T <sub>j</sub> =25°C		25	100		25	100	pА
I <sub>OS</sub>	Input Offset Current	$V_{S}=\pm 15V^{(1)(2)}$ $V_{S}=\pm 15V^{(1)(2)}$ $T_{j}=25^{\circ}C$ $R_{L}=2k, T_{A}=25^{\circ}C, V_{S}$	T <sub>j</sub> =70°C			2			2	nA
I <sub>B</sub> Inp			T <sub>j</sub> =125°C			25			25	nA
			T <sub>j</sub> =25°C		50	200		50	200	pА
I <sub>B</sub>	Input Bias Current	$V_{S}=\pm 15V^{(1)(2)}$	T <sub>j</sub> =70°C			4			4	nA
			T <sub>j</sub> =125°C			50			50	nA
R <sub>IN</sub>	Input Resistance	T <sub>j</sub> =25°C			10 <sup>12</sup>			10 <sup>12</sup>		Ω
A <sub>VOL</sub>	Large Signal	R <sub>L</sub> =2k, T <sub>A</sub> =25°C, V V <sub>O</sub> =±10V	R <sub>L</sub> =2k, T <sub>A</sub> =25°C, V <sub>S</sub> =±15V,		200		25	200		V/mV
	Voltage Gain	Over Temperature		25	200		15	200		
Vo	Output Voltage Swing	$V_S=\pm 15V, R_L=10k$		±12	±13.5		±12	±13.5		V
V	Input Common-Mode			±16	+19.5		±11	+14.5		V
V <sub>CM</sub>	Voltage Range				-16.5			-11.5		V
CMRR	Common-Mode Rejection Ratio	R <sub>S</sub> ≤10k		80	100		70	100		dB
PSRR	Supply Voltage Rejection Ratio	See <sup>(3)</sup>		80	100		70	100		dB
ls	Supply Current	$V_0 = 0V, R_L = \infty$			3.6	5.6		3.6	6.5	mA

(1) Unless otherwise specified, the specifications apply over the full temperature range and for  $V_S=\pm 20V$  for the LF412A and for  $V_S=\pm 15V$  for the LF412.  $V_{OS}$ ,  $I_B$ , and  $I_{OS}$  are measured at  $V_{CM}=0$ .

(2) The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T<sub>j</sub>. Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, P<sub>D</sub>. T<sub>j</sub>=T<sub>A</sub>+θ<sub>jA</sub> P<sub>D</sub> where θ<sub>jA</sub> is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

(3) Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously in accordance with common practice.  $V_S = \pm 6V$  to  $\pm 15V$ .

## 6.6 AC Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		LF412A <sup>(1)</sup>			L	UNIT		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Amplifier to Amplifier Coupling	T <sub>A</sub> =25°C, f=1 Hz-20 kHz (Input Referred)		-120			-120		dB

(1) Unless otherwise specified, the specifications apply over the full temperature range and for  $V_S=\pm 20V$  for the LF412A and for  $V_S=\pm 15V$  for the LF412.  $V_{OS}$ ,  $I_B$ , and  $I_{OS}$  are measured at  $V_{CM}=0$ .



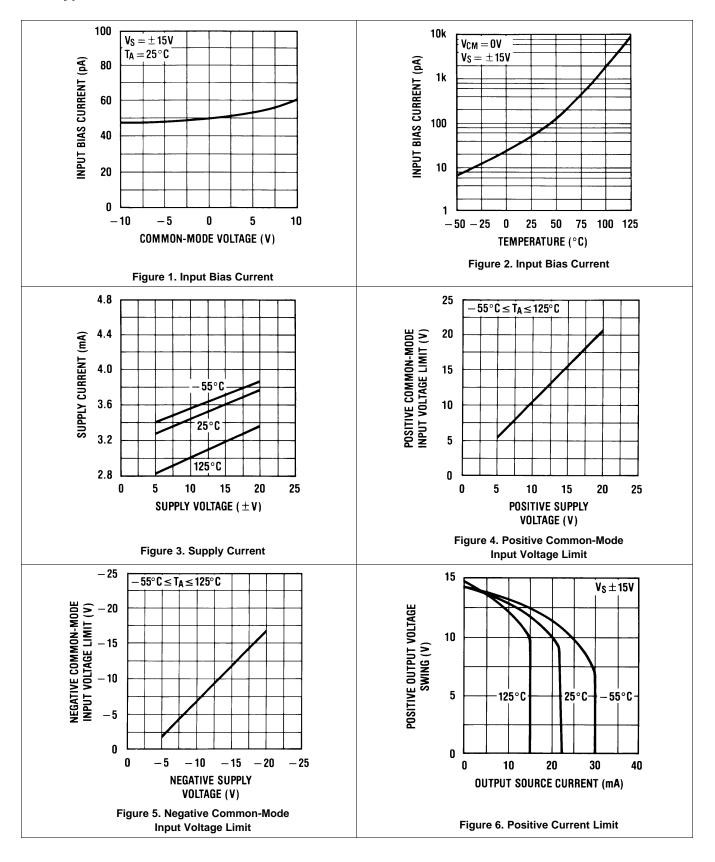
## **AC Electrical Characteristics (continued)**

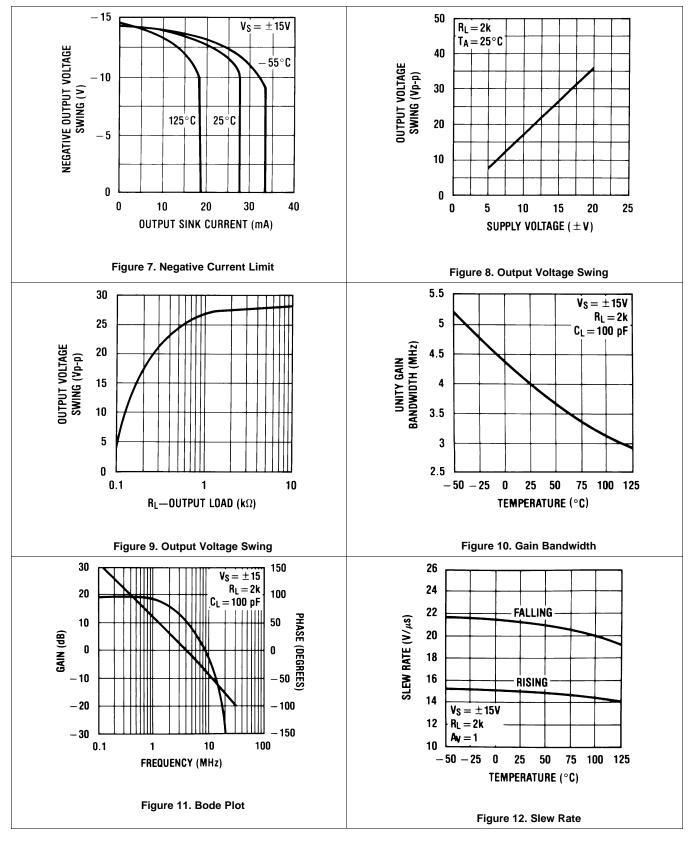
over operating free-air temperature range (unless otherwise noted)

		TEST CONDITIONS	L	F412A <sup>(1)</sup>		LF412 <sup>(1)</sup>			LINUT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
SR	Slew Rate	$V_S=\pm 15V, T_A=25^{\circ}C$	10	15		8	15		V/µs
GBW	Gain-Bandwidth Product	V <sub>S</sub> =±15V, T <sub>A</sub> =25°C	3	4		2.7	4		MHz
THD	Total Harmonic Dist	A <sub>V</sub> =+10, R <sub>L</sub> =10k, V <sub>O</sub> =20 Vp-p, BW=20 Hz-20 kHz	≤0.02%						
e <sub>n</sub>	Equivalent Input Noise Voltage	$T_A=25^{\circ}C, R_S=100\Omega, f=1 \text{ kHz}$		25			25		nV / √Hz
i <sub>n</sub>	Equivalent Input Noise Current	T <sub>A</sub> =25°C, f=1 kHz		0.01			0.01		pA / √Hz

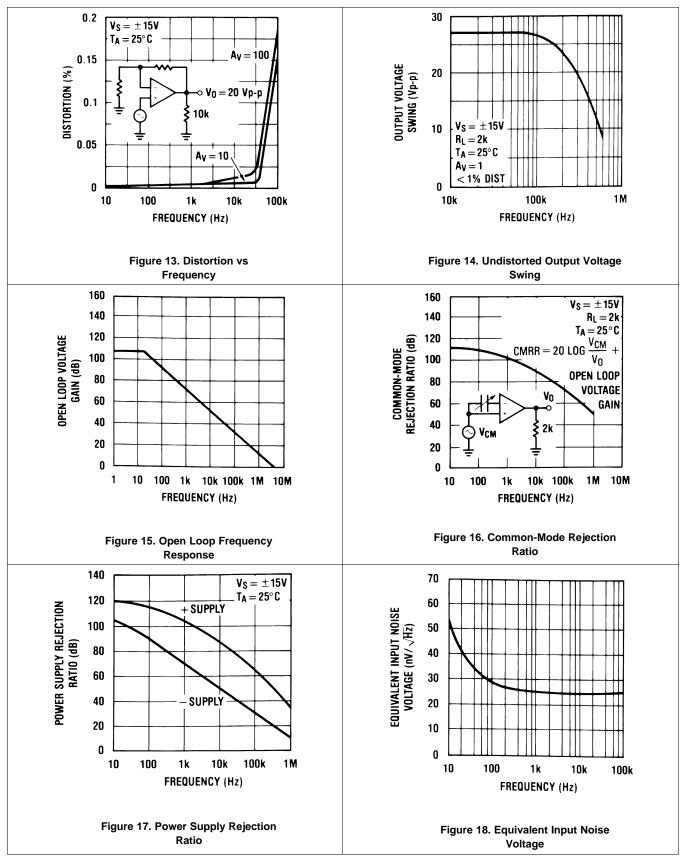


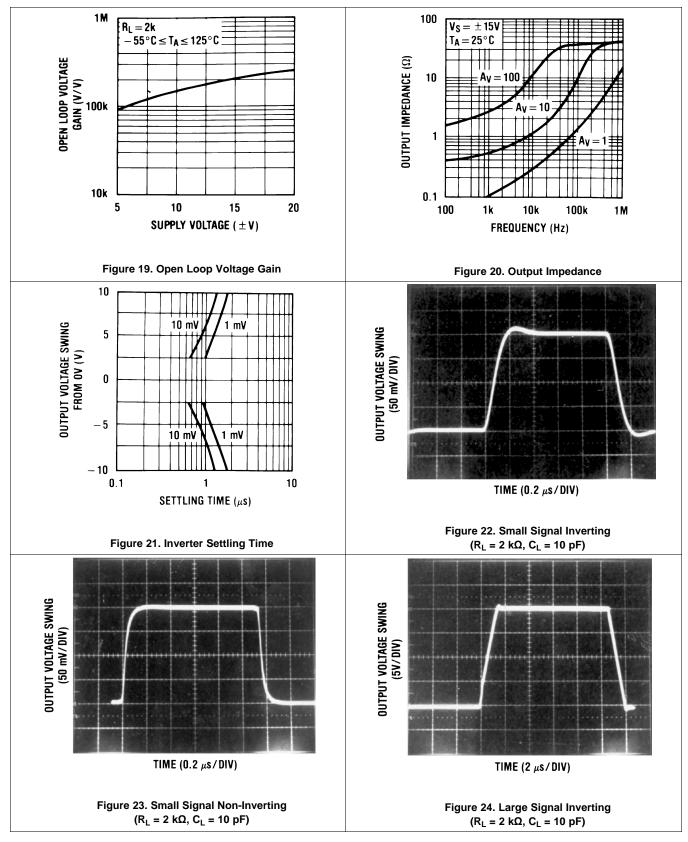
### 6.7 Typical Characteristics



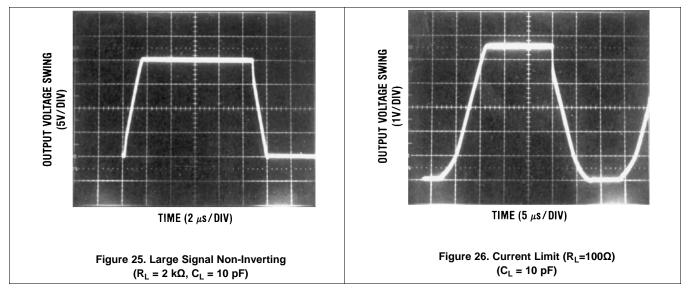












TEXAS INSTRUMENTS

www.ti.com

### 7 Detailed Description

### 7.1 Overview

The LF412 devices are low cost, high speed, JFET input operational amplifiers with very low input offset voltage and input offset voltage drift. They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF412-N dual is pin compatible with the LM1558, allowing designers to immediately upgrade the overall performance of existing designs.

These amplifiers may be used in applications such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage and drift, low input bias current, high input impedance, high slew rate and wide bandwidth.

### 7.2 Functional Block Diagram

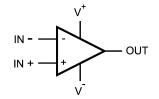


Figure 27. Each Amplifier

### 7.3 Feature Description

The amplifier's differential inputs consist of a non-inverting input (+IN) and an inverting input (-IN). The amplifier amplifies only the difference in voltage between the two inputs, which is called the differential input voltage. The output voltage of the op-amp V<sub>OUT</sub> is given by the equation  $V_{OUT} = A_{OL}(IN + -IN)$ .



## 7.4 Device Functional Modes

## 7.4.1 Input and Output Stage

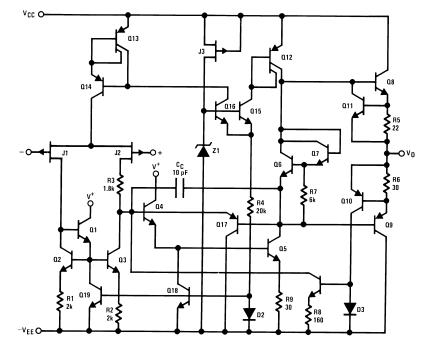


Figure 28. 1/2 Dual LF412

Texas Instruments

www.ti.com

### 8 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The LF412-N series of JFET input dual op amps are internally trimmed (BI-FET II<sup>™</sup>) providing very low input offset voltages and input offset voltage drift. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore, large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

### 8.2 Typical Application

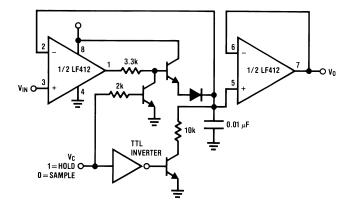


Figure 29. Single Supply Sample and Hold

### 8.2.1 Design Requirements

Single supply.

### 8.2.2 Detailed Design Procedure

Exceeding the negative common-mode limit on either input will cause a reversal of the phase to the output and force the amplifier output to the corresponding high or low state.

Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output, however, if both inputs exceed the limit, the output of the amplifier may be forced to a high state.

The amplifiers will operate with a common-mode input voltage equal to the positive supply; however, the gain bandwidth and slew rate may be decreased in this condition. When the negative common-mode voltage swings to within 3V of the negative supply, an increase in input offset voltage may occur.

Each amplifier is individually biased by a zener reference which allows normal circuit operation on  $\pm 6.0V$  power supplies. Supply voltages less than these may result in lower gain bandwidth and slew rate.

The amplifiers will drive a 2 k $\Omega$  load resistance to ±10V over the full temperature range. If the amplifier is forced to drive heavier load currents, however, an increase in input offset voltage may occur on the negative voltage swing and finally reach an active current limit on both positive and negative swings.

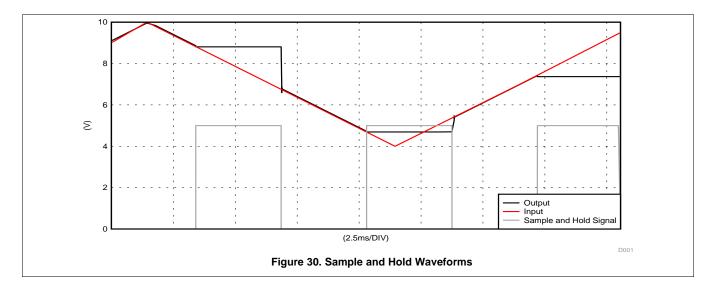


### **Typical Application (continued)**

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately 6 times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.



### 8.2.3 Application Curves



### 9 Power Supply Recommendations

For proper operation, the power supplies must be properly decoupled. For decoupling the supply lines it is suggested that  $0.1\mu$ F capacitors be placed as close as possible to the op amp power supply pins. The minimum power supply voltage is ±5V.

## 10 Layout

### 10.1 Layout Guidelines

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

### 10.2 Layout Example

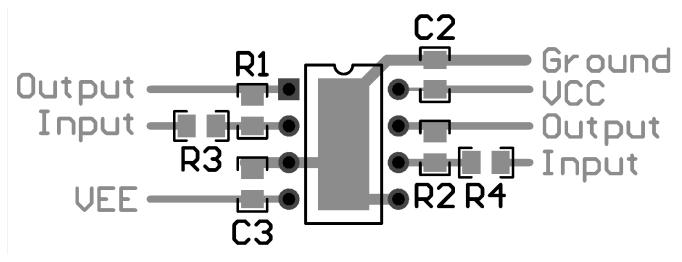


Figure 31. LF412 Layout



### **11** Device and Documentation Support

### 11.1 Trademarks

BI-FET II is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

### **11.2 Electrostatic Discharge Caution**



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 11.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

### 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



29-Jun-2017

## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LF412ACN/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LF 412ACN	Samples
LF412CN/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LF 412CN	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



# PACKAGE OPTION ADDENDUM

29-Jun-2017

P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



#### **IMPORTANT NOTICE**

Texas Instruments Incorporated (TI) reserves the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete.

TI's published terms of sale for semiconductor products (http://www.ti.com/sc/docs/stdterms.htm) apply to the sale of packaged integrated circuit products that TI has qualified and released to market. Additional terms may apply to the use or sale of other types of TI products and services.

Reproduction of significant portions of TI information in TI data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such reproduced documentation. Information of third parties may be subject to additional restrictions. Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyers and others who are developing systems that incorporate TI products (collectively, "Designers") understand and agree that Designers remain responsible for using their independent analysis, evaluation and judgment in designing their applications and that Designers have full and exclusive responsibility to assure the safety of Designers' applications and compliance of their applications (and of all TI products used in or for Designers' applications) with all applicable regulations, laws and other applicable requirements. Designer represents that, with respect to their applications, Designer has all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. Designer agrees that prior to using or distributing any applications that include TI products, Designer will thoroughly test such applications and the functionality of such TI products as used in such applications.

TI's provision of technical, application or other design advice, quality characterization, reliability data or other services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using TI Resources in any way, Designer (individually or, if Designer is acting on behalf of a company, Designer's company) agrees to use any particular TI Resource solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

Designer is authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS. TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY DESIGNER AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

Unless TI has explicitly designated an individual product as meeting the requirements of a particular industry standard (e.g., ISO/TS 16949 and ISO 26262), TI is not responsible for any failure to meet such industry standard requirements.

Where TI specifically promotes products as facilitating functional safety or as compliant with industry functional safety standards, such products are intended to help enable customers to design and create their own applications that meet applicable functional safety standards and requirements. Using products in an application does not by itself establish any safety features in the application. Designers must ensure compliance with safety-related requirements and standards applicable to their applications. Designer may not use any TI products in life-critical medical equipment unless authorized officers of the parties have executed a special contract specifically governing such use. Life-critical medical equipment is medical equipment where failure of such equipment would cause serious bodily injury or death (e.g., life support, pacemakers, defibrillators, heart pumps, neurostimulators, and implantables). Such equipment includes, without limitation, all medical devices identified by the U.S. Food and Drug Administration as Class III devices and equivalent classifications outside the U.S.

TI may expressly designate certain products as completing a particular qualification (e.g., Q100, Military Grade, or Enhanced Product). Designers agree that it has the necessary expertise to select the product with the appropriate qualification designation for their applications and that proper product selection is at Designers' own risk. Designers are solely responsible for compliance with all legal and regulatory requirements in connection with such selection.

Designer will fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of Designer's noncompliance with the terms and provisions of this Notice.

> Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2017, Texas Instruments Incorporated